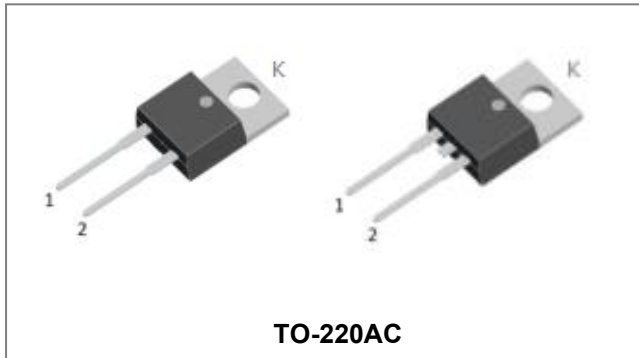


MBR10150 SCHOTTKY RECTIFIER



Features

- 175°C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced
- mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: Tin Lead-free plated
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings@T_c=25°C unless otherwise specified

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V _{RRM}	-	150	V
Working Peak Reverse Voltage	V _{RWM}			
DC Blocking Voltage	V _R			
Average Rectified Forward Current	I _{F(AV)}	T _c =153°C, In DC	10	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	138	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 10A, Pulse, T _J = 25 °C	0.84	1.1	V
	V _{F2}	@ 10A, Pulse, T _J = 125 °C	0.75	0.86	V
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.001	1.0	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	0.1	7.0	mA
Non-Repetitive Avalanche Energy	E _{AS}	T _J = 25 °C, I _{AS} = 2 A, L = 1mH	-	2	mJ
Junction Capacitance	C _T	@V _R = 5V, T _c = 25 °C f _{sig} = 1MHz	170	200	pF
Series Inductance	L _S	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 μs, duty cycle < 2%

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +175	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	DC operation	2	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	1.6	g
Case Style	TO-220AC			

Ratings and Characteristics Curves

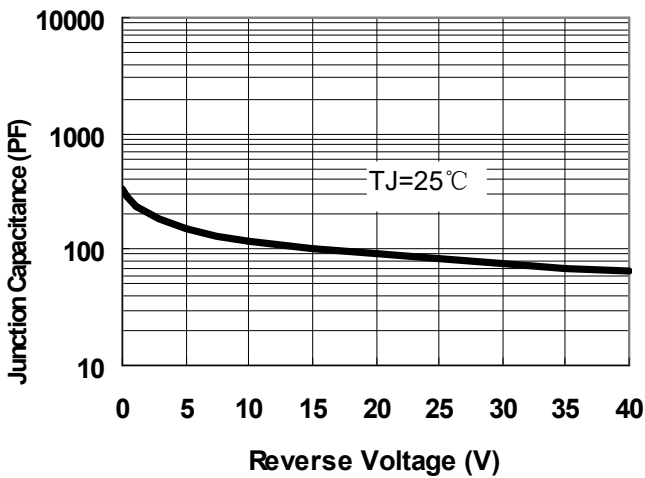


Fig.1-Typical Junction Capacitance

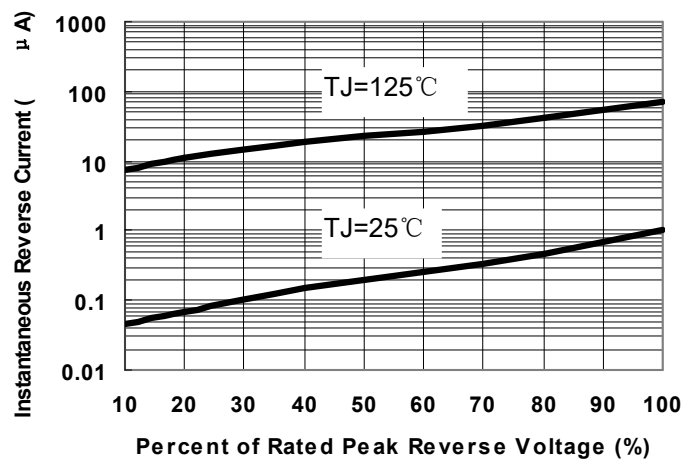


Fig.2-Typical Reverse Characteristics

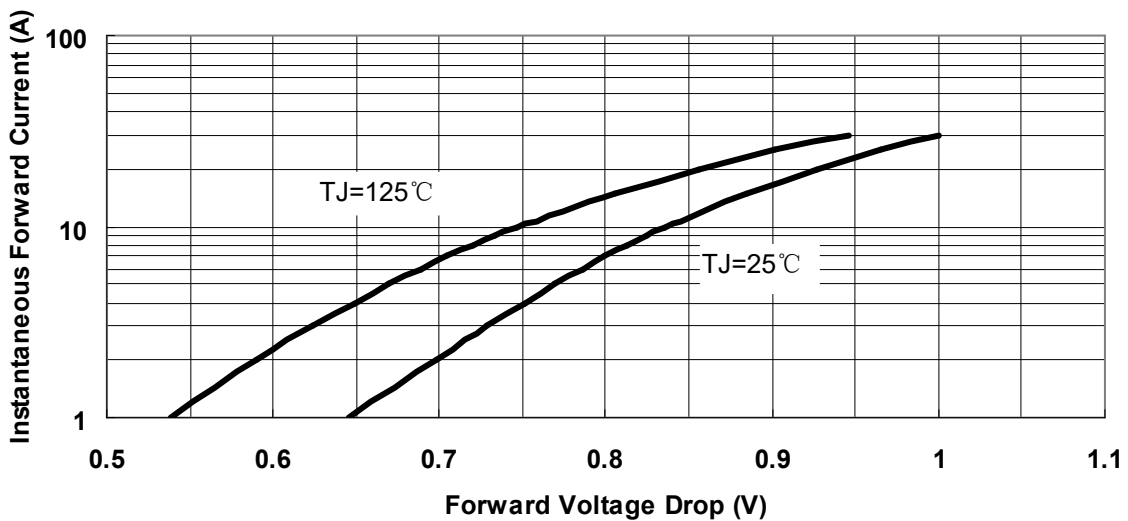
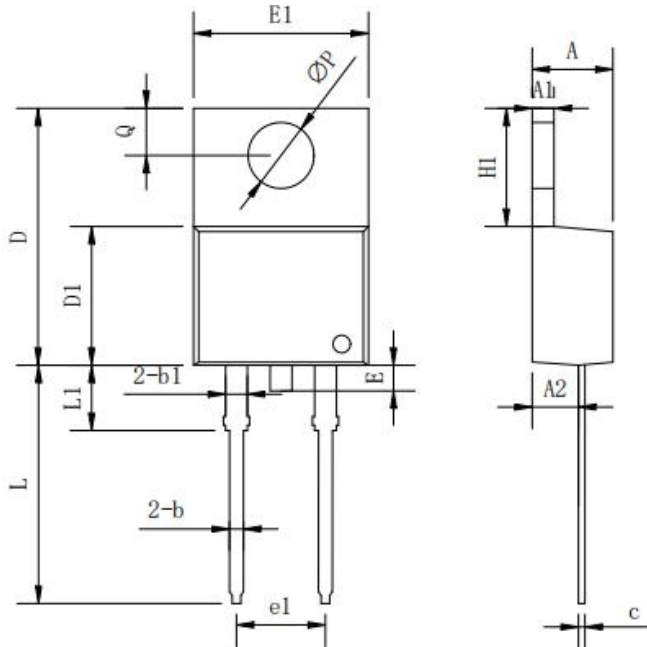


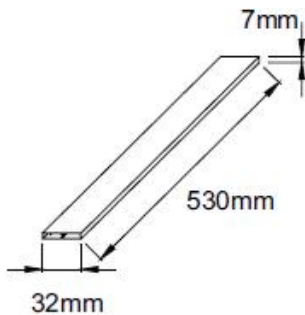
Fig.3-Typical Instantaneous Forward Voltage Characteristics

Mechanical Dimensions TO-220AC



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	3.56	-	4.83
A1	0.51	-	1.4
A2	2.03	-	2.92
b	0.38	-	1.02
b1	1.14	-	1.78
c	0.31	-	0.61
D	14.22	-	16.51
D1	8.38	-	9.42
E	-	-	1.78
E1	9.65	10.16	10.67
e1	-	5.08	-
H1	5.84	-	6.86
L	12.7	-	14.73
L1	-	-	6.35
ΦP	-	3.56	-
Q	2.54	-	3.43

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

- MBR = Device Type
- 10 = Forward Current (10A)
- 150 = Reverse Voltage(150V)
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
MBR10150	TO-220AC (Pb-Free)	50 pcs/ tube

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